Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring good bidirectional blocking voltage capability, high surge current capability, high junction temperature capability and high thermal cycling performance.

2. Features and benefits

- Good bidirectional blocking voltage capability
- · High junction operating temperature capability
- · High surge current capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability

3. Applications

- Capacitive Discharge Ignition (CDI)
- · Crowbar protection
- · Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DRM}	repetitive peak off- state voltage			-	-	500	V	
V_{RRM}	repetitive peak reverse voltage			-	-	500	V	
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms		-	-	132	А	
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5		-	-	120	А	
Tj	junction temperature			-	-	150	°C	
$I_{T(AV)}$	average on-state current	half sine wave; T _{mb} ≤ 133 °C		-	-	8	А	
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 133 \text{ °C}$; $\overline{Fig. 1}$; $\overline{Fig. 2}$; $\overline{Fig. 3}$		-	-	12.5	А	
Static characteristics								
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$		-	2	15	mA	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic chara	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 335 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); gate open circuit; exponential waveform; Fig. 12	-	300	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	А Ы К
2	Α	anode	├	G sym037
3	G	gate		symoor.
mb	A	mounting base; connected to anode	TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package	ackage					
	Name	Description	Version				
BT151-500RT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	500	V
V_{RRM}	repetitive peak reverse voltage		-	500	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 133 °C	-	8	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 133 \text{ °C}$; $\overline{Fig. 1}$; $\overline{Fig. 2}$; $\overline{Fig. 3}$	-	12.5	Α
I _{TSM}	non-repetitive peak on-	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms	-	132	Α
	state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	120	Α
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	72	A²s
dl _T /dt	rate of rise of on-state current	I _G = 30 mA	-	50	A/µs
I _{GM}	peak gate current		-	4	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C

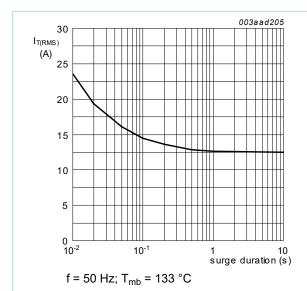


Fig. 1. RMS on-state current as a function of surge duration; maximum values

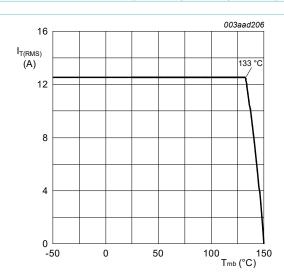


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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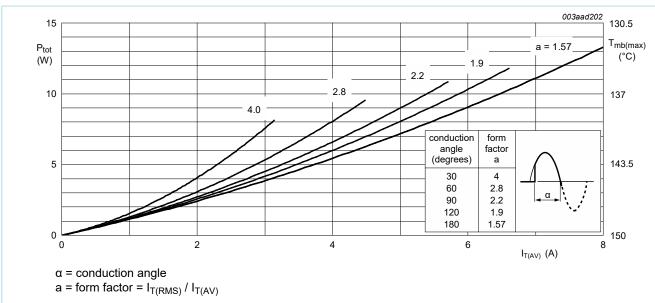


Fig. 3. Total power dissipation as a function of average on-state current; maximum values

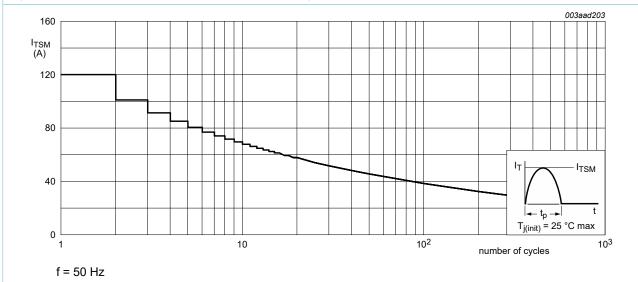
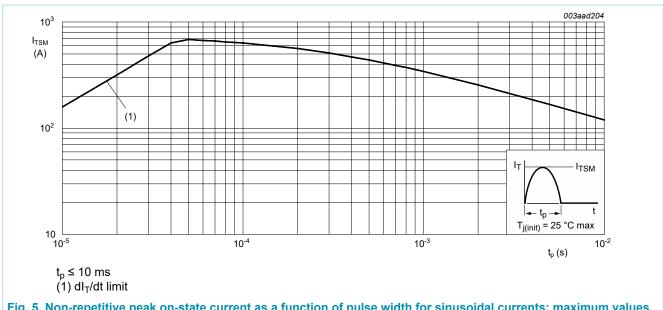


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6	-	-	1.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

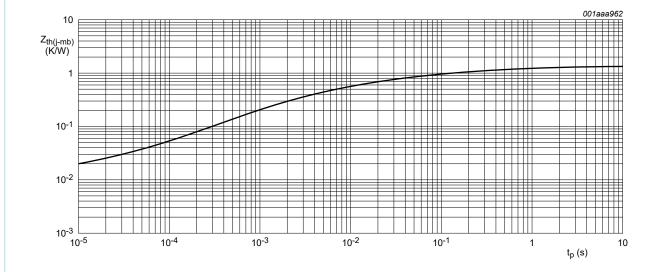


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

i able 6. Cha	aracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			,		,
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 7</u>	-	2	15	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 8$	-	10	40	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	7	20	mA
V _T	on-state voltage	I _T = 23 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.75	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11	-	0.6	1	V
		$V_D = 500 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 500 V; T _j = 150 °C	-	0.5	2.5	mA
I _R	reverse current	V _R = 500 V; T _j = 150 °C	-	0.5	2.5	mA
Dynamic ch	naracteristics			'		
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 335 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); gate open circuit; exponential waveform; Fig. 12	-	300	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 40 A; V_D = 500 V; I_G = 0.1 A; dI_G/dt = 5 A/µs; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 335 V; T_j = 150 °C; I_{TM} = 20 A; V_R = 25 V; $(dI_T/dt)_M$ = 30 A/µs; dV_D/dt = 50 V/µs; $R_{GK(ext)}$ = 100 Ω ; $(V_{DM}$ = 67% of $V_{DRM})$	-	70	-	μs

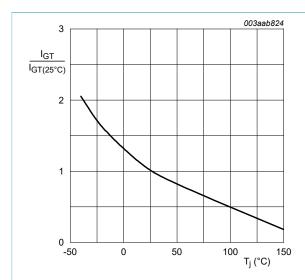


Fig. 7. Normalized gate trigger current as a function of junction temperature

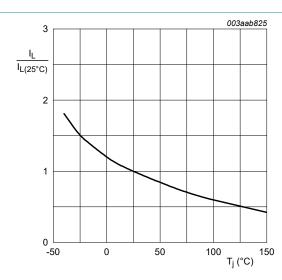


Fig. 8. Normalized latching current as a function of junction temperature

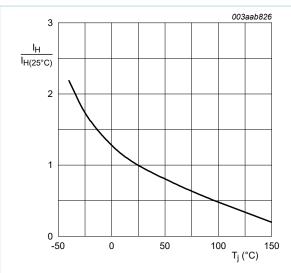
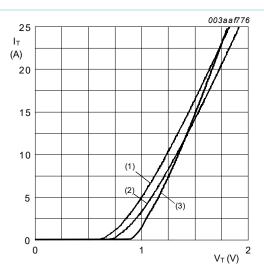


Fig. 9. Normalized holding current as a function of junction temperature



Vo = 0.825 V; Rs = 0.41 Ω

(1) Tj = 150°C; typical values

(2) Tj = 150°C; maximum values

(3) Tj = 25°C; maximum values

Fig. 10. On-state current as a function of on-state voltage

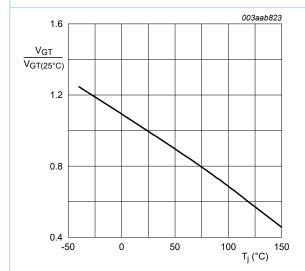


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

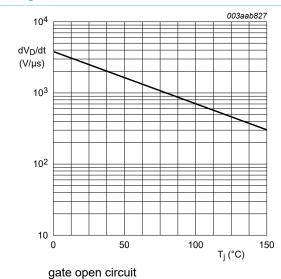
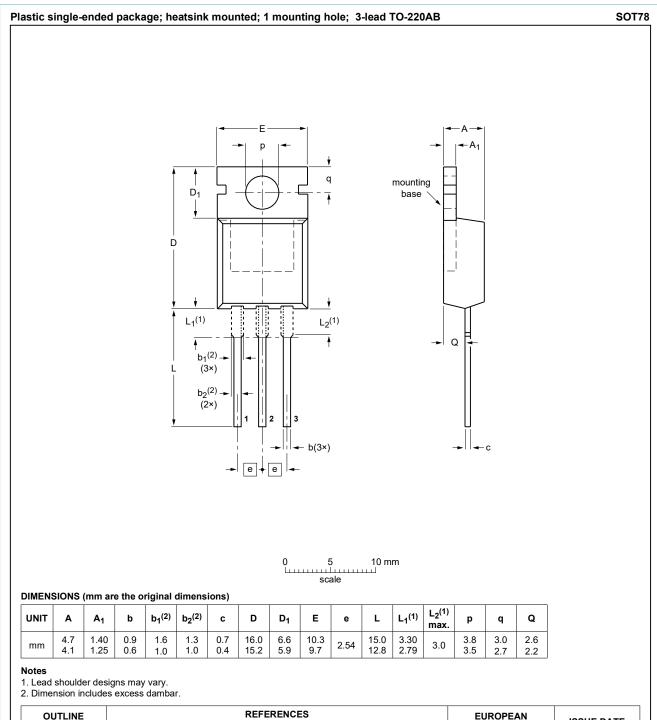


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

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10. Package outline



VERSION IEC JEDEC JEITA PROJECTION SOT78 3-lead TO-220AB SC-46	OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
SO1/8 3 load TO 220AB $SC-46$ $+-++H+H$	VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
	SOT78		3-lead TO-220AB	SC-46		

Fig. 13. Package outline TO-220AB (SOT78)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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